

L Number	Hits	Search Text	DB	Time stamp
1	306	(257/64).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 10:42
-	2	("6160279").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:46
-	15612	catalyst near4 concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:16
-	1050521	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:16
-	407	(catalyst near4 concentration) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:35
-	1546424	group	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:16
-	294	((catalyst near4 concentration) and semiconductor) and group	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:17
-	1297	semiconductor adj energy adj laboratory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:17
-	33750	((thin adj film adj transistor) or (tft))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:19
-	62	((catalyst near4 concentration) and semiconductor) and group) and (semiconductor adj energy adj laboratory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:19
-	87	((catalyst near4 concentration) and semiconductor) and group) and ((thin adj film adj transistor) or (tft))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/17 12:19
-	287715	nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 13:30
-	7	fonash.in. and nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 13:34
-	14	("5112764") or ("5275851") or ("5330935") or ("5403772") or ("5426064")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 13:35

-	89843	crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:21
-	34295	amorphous adj silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:21
-	1636	crystallization same (amorphous adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:21
-	805693	nickel or iron or platinum or cobalt or paladium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:23
-	614	(crystallization same (amorphous adj silicon)) and (nickel or iron or platinum or cobalt or paladium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:29
-	216	"oka hideaki"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:29
-	3	(nickel or iron or platinum or cobalt or paladium) and "oka hideaki"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:30
-	79875	"seiko epson"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:31
-	2167	(nickel or iron or platinum or cobalt or paladium) and "seiko epson"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/09 17:45
-	33821	((thin adj film adj transistor) or (tft))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/10 09:40
-	3	crystallization and ((nickel or iron or platinum or cobalt or paladium) and "seiko epson") and (((thin adj film adj transistor) or (tft)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:38
-	27773	crystallization and (nickel or iron or platinum or cobalt or paladium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:38
-	1036	(amorphous adj silicon) and (crystallization and (nickel or iron or platinum or cobalt or paladium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 14:38
-	568	((((thin adj film adj transistor) or (tft))) and ((amorphous adj silicon) and (crystallization and (nickel or iron or platinum or cobalt or paladium)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 15:13




-	177	5147826.uref.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 15:31
-	10	((("4693759") or ("4814292") or ("4904611") or ("4902642"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 15:31
-	2057040	carbon or silicon or germanium or lead	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:35
-	357	((catalyst near4 concentration) and semiconductor) and (carbon or silicon or germanium or lead)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:47
-	590297	catalyst	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:47
-	236760	(carbon or silicon or germanium or lead) and catalyst	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:48
-	3419	crystallizing and ((carbon or silicon or germanium or lead) and catalyst)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:48
-	237	amorphous adj silicon and (crystallizing and ((carbon or silicon or germanium or lead) and catalyst))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:48
-	73	lead and (amorphous adj silicon and (crystallizing and ((carbon or silicon or germanium or lead) and catalyst)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2001/09/22 16:49
-	46	fonash.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/08 14:26
-	61374	crystal same direction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/08 14:27
-	1125231	mosfet or semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/08 14:27
-	15233	(crystal same direction) and (mosfet or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/08 14:28
-	243432	crystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/08 14:28

-	3360	((crystal same direction) and (mosfet or semiconductor)) and crystalline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 14:28
-	196185	source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 14:28
-	196185	(source and drain) and (source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 14:29
-	923	((crystal same direction) and (mosfet or semiconductor)) and crystalline) and (source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 14:30
-	710724	concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 14:30
-	660	((crystal same direction) and (mosfet or semiconductor)) and crystalline) and (source and drain)) and concentration	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 14:32
-	13	("3108914"   "3389024"   "3783049"   "3873384"   "3886569"   "3988762"   "4090915"   "4091527"   "4110488"   "4619719"   "5147826"   "5275851"   "5403772").PN.	USPAT	2002/04/08 15:07
-	203	5147826.URPN.	USPAT	2002/04/08 15:11
-	1506	yonehara.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 16:19
-	11976717	pb or sn or c or ge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 16:21
-	1248	yonehara.in. and (pb or sn or c or ge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 16:23
-	40857	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 16:24
-	16	(yonehara.in. and (pb or sn or c or ge)) and (tft or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/08 16:24
-	67	5278093.URPN.	USPAT	2002/04/08 16:31
-	4	("3900345"   "4151008"   "4897360"   "4915772").PN.	USPAT	2002/04/08 16:57
-	5	5212101.uref.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/04/09 14:07

-	35	("3692574"   "4727044"   "4904611"   "4986213"   "5145808"   "5147826"   "5212101"   "5242858"   "5262350"   "5275851"   "5278093"   "5288658"   "5296405"   "5318661"   "5403772"   "5426064"   "5457058"   "5476799"   "5501989"   "5508533"   "5531182"   "5534716"   "5545571"   "5569936"   "5589694"   "5597741"   "5604360"   "5739590"   "5773846"   "5789762"   "5808321"   "5818076"   "5859443"   "5895933"   "5932893").PN.	USPAT	2002/04/09 14:08
-	13	("4072974"   "4113514"   "4196438"   "4239554"   "4377902"   "4406709"   "4463492"   "4470060"   "4476475"   "4514895"   "4598304"   "4619034"   "4667217").PN.	USPAT	2002/04/09 14:21
-	2	("3692574").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/09 16:27
-	2	("6160279").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/09 17:10
-	1486312	connecting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/09 17:10
-	1	((("6160279").PN.) and connecting	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/09 17:11
-	67	((nickel or iron or platinum or cobalt or paladium) and "seiko epson") and (active adj matrix or image adj sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/09 17:47
-	17202	sims or ("secondary ion mass spectroscopy")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/10 09:40
-	451	((thin adj film adj transistor) or (tft)) and (sims or ("secondary ion mass spectroscopy"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/10 09:42
-	11	"threshold" near germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:48
-	47750	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:49
-	2	("5422302").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:54
-	1543	yonehara.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:54

-	1197095	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:55
-	509	yonehara.in. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:55
-	138539	pb	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:55
-	1	(yonehara.in. and semiconductor) and pb	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:55
-	228175	sn or pb	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:55
-	44	(yonehara.in. and semiconductor) and (sn or pb)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/19 14:57
-	0	yonehara and pb and sn	EPO; DERWENT	2003/02/19 14:57
-	79107	sn or pb	EPO; DERWENT	2003/02/19 14:57
-	6	yonehara.in. and (sn or pb)	EPO; DERWENT	2003/02/19 14:57
-	360	yonehara.in.	EPO; DERWENT	2003/02/20 09:47
-	2	("6160279").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/10 09:43

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Date	Code	Status	Status2	App #	Sender	Team	Text
09/10/2004	ADHO C	closed		09/726337	JWILLIAM S3	2800TSS01 LIE	after final enter in plam
09/10/2004	RUSH	closed		09/764913	OCHAUD HURI	2823Examin ation	PRINTER RUSH
09/07/2004	A.NE	open		09/726337	SHOPPE	2800SPRE	dist is approved.